



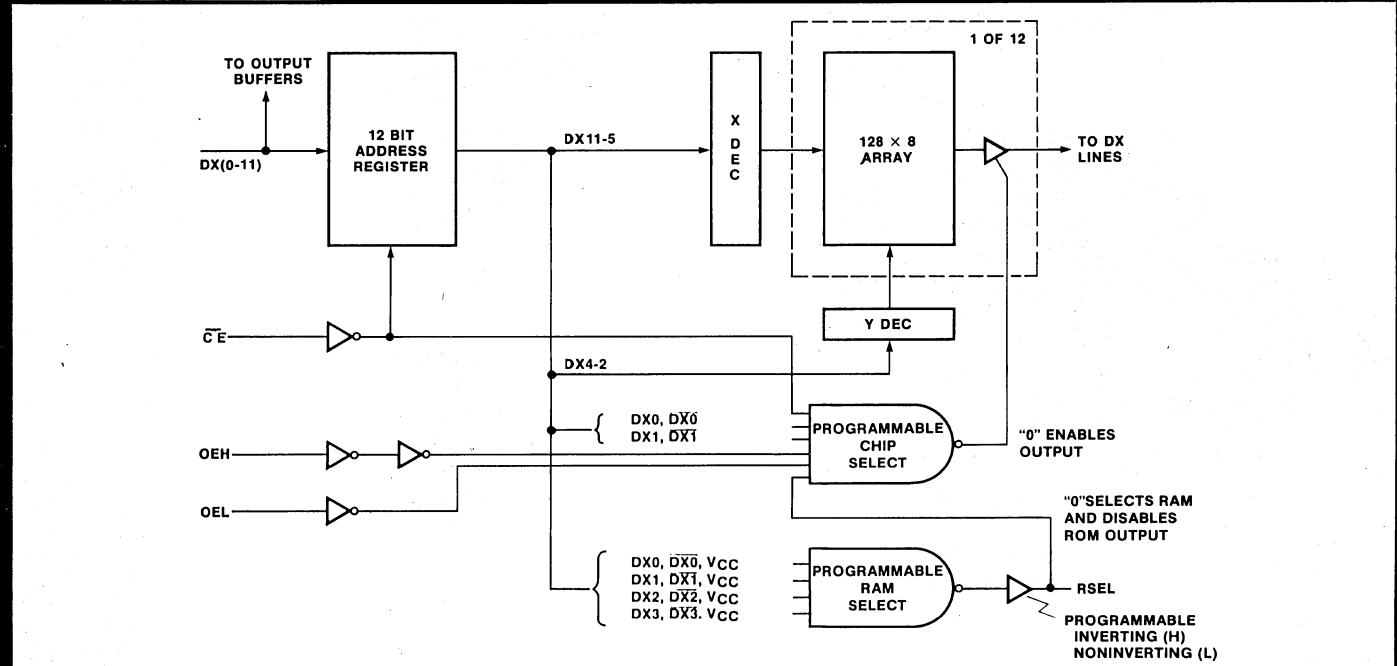
HARRIS
SEMICONDUCTOR
A DIVISION OF HARRIS CORPORATION

PRELIMINARY
HM-6312/6312A
CMOS ROM
1024 WORD x 12 BIT

| FEATURES | PINOUT/PACKAGE |
|--|--|
| <ul style="list-style-type: none"> • HM-6100 COMPATIBLE • LOW POWER - TYP. < 5.0 μW STANDBY • 4 - 11 VOLT V_{CC} OPERATION • HIGH SPEED • STATIC OPERATION | <p>18 LEAD CERAMIC D. I. P.</p> <p>NOTE: Board drilling dimensions will equal standard practice for .020 diameter lead.</p> |

| DESCRIPTION | OPERATION |
|---|---|
| <p>The HM-6312 and HM-6312A are high speed, low power, silicon gate CMOS static ROM's organized 1024 words by 12 bits. In all static states these units exhibit the microwatt power requirements typical of CMOS. The basic part operates at 4 - 7 Volts with a typical 5 Volt 25°C access time of 350 ns. Higher operating voltages, 4 - 11 Volts, are available with the A version. Signal polarities and functions are specified for interfacing with the HM-6100 Micro-processor.</p> | <p>Addresses and data out are multiplexed on 12 lines, DX0 - DX11. Addresses are loaded into an on chip register by the falling edge of \overline{CE}. Data out, corresponding to the latched address, is enabled when \overline{CE} and OEL are low and OEH is high and the decoded state of DX0 and DX1 are true. The RSEL output defines an area in the 4096 word addressing space dedicated to RAM. It can be programmed by DX0, DX1, DX2, and DX3. This output eliminates a four bit register and decoder for the high order address bits to select RAM.</p> |

FUNCTIONAL DIAGRAM



SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS

| | |
|---------------------------------|-------------------------------|
| Supply Voltage | |
| Supply Voltage HM-6312 | + 8.0V |
| Supply Voltage HM-6312A | + 12.0V |
| Applied Input or Output Voltage | GND - 0.3V to $V_{CC} + 0.3V$ |
| Storage Temperature Range | |
| Industrial HM-6312/6312A-9 | - 40°C to + 85°C |
| Military HM-6312/6312A-2 | - 55°C to + 125°C |

D. C. CHARACTERISTICS $V_{CC} = 4-7V$ (HM-6312); $V_{CC} = 4-11V$ (HM-6312A)

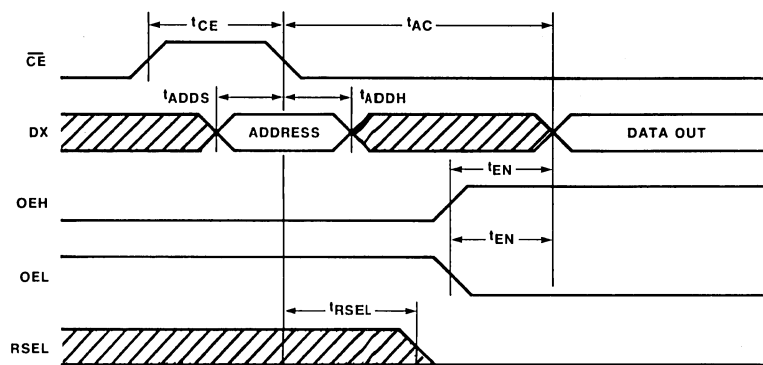
| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNITS | TEST CONDITIONS |
|----------------------------|-----------|----------------|------|--------------|---------|------------------------------|
| Logical "1" Input Voltage | V_{IH} | 70% V_{CC} | | | V | |
| Logical "0" Input Voltage | V_{IL} | | | 20% V_{CC} | V | |
| Input Leakage | I_{IL} | -1.0 | | +1.0 | μA | $0V \leq V_{IN} \leq V_{CC}$ |
| Logical "1" Output Voltage | V_{OH} | $V_{CC} - 0.1$ | | | V | $I_{OUT} = 0$ |
| Logical "0" Output Voltage | V_{OL} | | | GND + .01 | V | $I_{OUT} = 0$ |
| Output Leakage | I_O | -1.0 | | 1.0 | μA | $0V \leq V_{IN} \leq V_{CC}$ |
| Supply Current | I_{CC} | | 1.0 | | μA | $V_{IN} = 0$ or V_{CC} |
| Input Capacitance* | C_{IN} | | 5.0 | 7.0 | pF | |
| Output Capacitance* | C_{OUT} | | 6.0 | 10.0 | pF | |

*Guaranteed and sampled, but not 100% tested.

A. C. CHARACTERISTICS $T_A = 25^\circ C$, $C_L = 50pF$

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNITS | TEST CONDITIONS |
|------------------------------------|------------|------|------|------|-------|------------------|
| Access Time From CE (6312) | t_{AC} | | 500 | | ns | $V_{CC} = 5.0V$ |
| (6312A) | | | 250 | | ns | $V_{CC} = 10.0V$ |
| Output Enable Time (6312) | t_{EN} | | 250 | | ns | $V_{CC} = 5.0V$ |
| (6312A) | | | 125 | | ns | $V_{CC} = 10.0V$ |
| Strobe Positive Pulse Width (6312) | t_{CE} | | 220 | | ns | $V_{CC} = 5.0V$ |
| (6312A) | | | 110 | | ns | $V_{CC} = 10.0V$ |
| Address Set-Up Time (6312) | t_{ADDS} | | 50 | | ns | $V_{CC} = 5.0V$ |
| (6312A) | | | 25 | | ns | $V_{CC} = 10.0V$ |
| Address Hold Time (6312) | t_{ADDH} | | 50 | | ns | $V_{CC} = 5.0V$ |
| (6312A) | | | 25 | | ns | $V_{CC} = 10.0V$ |
| Propagation To RAM Select (6312) | t_{RS} | | 250 | | ns | $V_{CC} = 5.0V$ |
| (6312A) | | | 125 | | ns | $V_{CC} = 10.0V$ |

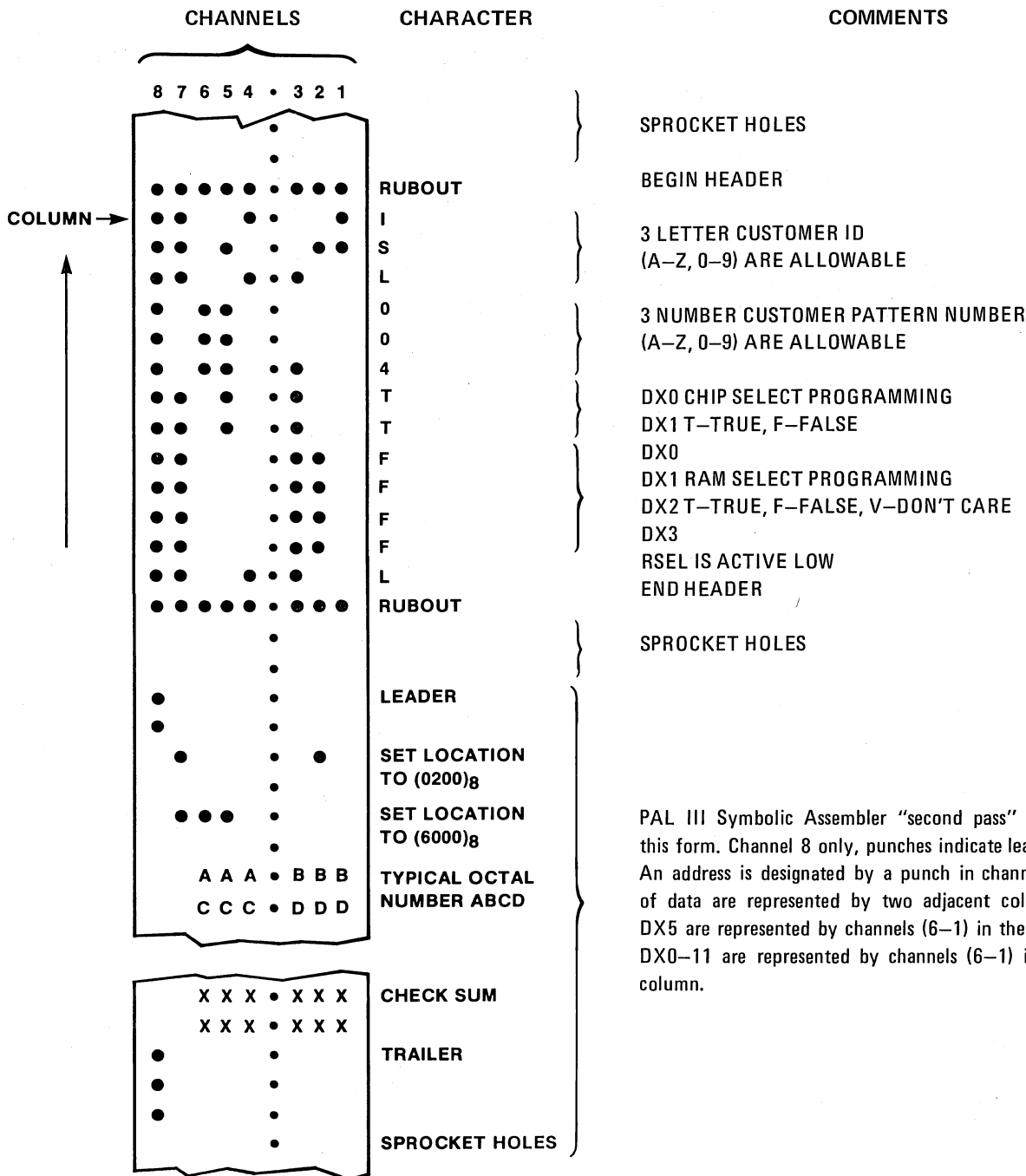
SWITCHING WAVEFORMS



CUSTOM ROM PROGRAMMING

HM-6312/6312A programming information is generated from the PAL III Symbolic Assembler as a "second pass" binary tape. A separate tape is required for each 1024 word ROM pattern, i. e. a separate symbolic should be generated for each 1024 word block of memory used, (0000-1777)₈, (2000-3777)₈, (4000-5777)₈ and (6000-7777)₈. A header is added to the front of each tape giving customer ID, chip select and RAM select programming information. The header consists of 15 ASCII characters generated from a standard teletype. Channel 8 is always punched. The header begins

with a rubout followed by 6 alphanumeric characters identifying the customer and the pattern number. Next are 2 letters designating true, false or don't care for inputs DX0 and DX1 to chips select gate A (see functional diagram), and 4 letters designating true, false, don't care for inputs DX0, DX1, DX2, and DX3 to the RAM select gate B (see functional diagram). Next is one letter (H or L) designating RSEL as active high or active low. RSEL function is inhibited when all RSEL inputs are V_{CC} and RSEL is active high. The leader ends with a rubout.



The example shown above has a customer ID and pattern ISL 004. Chip selects are programmed to recognize addresses (6000-7777)₈ or (3073-4095)₁₀. RAM select is active low

for addresses (0000-0400)₈ or (0000-0255)₁₀. For programs using less 1024 words, the unused locations are automatically programmed to a logic one.

